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IN THE CLAIMS:

Please amend the claims as follows:

1. – 3. (Cancelled)

4. (Currently amended) ~~The method of claim 3, wherein~~ A method of modulating the flatband voltage of a high-k dielectric material of a semiconductor device, comprising the steps of:
depositing the high-k dielectric material on a surface; and
controllably modulating the flatband voltage of the high-k dielectric material by annealing the high-k dielectric material under controlled annealing parameters, wherein:
the controlled annealing parameters include at least one of: annealing temperatures;
annealing times; annealing gases; and number of anneals;
the annealing includes controlling the temperature of anneals about 400°C to about 1000°C; and
the annealing includes a plurality of anneals with a different annealing gas in each anneal.

5. (Original) The method of claim 4, wherein the annealing gases include at least one of: O₂, N₂, H₂ and NH₃.

6. (Original) The method of claim 5, wherein the annealing includes controlling the annealing time between 10 seconds to 60 seconds.

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7. (Currently amended) The method of claim 4, wherein the step of controlling modulating includes changing the flatband voltage by at least 0.3V.
8. (Currently amended) The method of claim 4, wherein the step of controllably modulating includes modulating the high-k dielectric material for P-channel devices to a first value and the high-k dielectric material for N-channel devices to a second value different from the first value.
9. (Currently amended) ~~The method of claim 8, wherein~~ A method of modulating the flatband voltage of a high-k dielectric material of a semiconductor device, comprising the steps of:
depositing the high-k dielectric material on a surface; and
controllably modulating the flatband voltage of the high-k dielectric material by annealing the high-k dielectric material under controlled annealing parameters, wherein the step of controllably modulating includes modulating the high-k dielectric material for P-channel devices to a first value and the high-k dielectric material for N-channel devices to a second value different from the first value, and the step of modulating the high-k dielectric material for P-channel devices to a first value includes annealing with N₂.
10. (Original) The method of claim 9, further comprising preventing exposure of the high-k dielectric material for N-channel devices to the N₂ during the step of modulating the high-k dielectric material for P-channel devices.
11. – 12. (Cancelled)

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13. (Currently amended) ~~The method of claim 12, wherein~~ A method for forming a semiconductor chip, comprising the steps of:
depositing a high-k dielectric film;
annealing to modify the flatband voltage of the high-k dielectric film to a first value for a first set of devices on the chip; and
annealing to modify the flatband voltage of the high-k dielectric film to a second value, different than the first value, for a second set of devices on the chip, wherein:
the first set of devices are N-channel devices and the second set of devices are P-channel devices; and
the step of annealing to modify the flatband voltage of the high-k dielectric film includes masking the N-channel devices and subjecting the P-channel devices to annealing with N₂.
14. (Original) The method of claim 13, further comprising subjecting both the N-channel devices and the P-channel devices to an annealing with NH₃ and an annealing with O₂.
15. (Original) The method of claim 14, further comprising subjecting both the N-channel devices and the P-channel devices to an annealing with H₂.
16. (Original) The method of claim 15, further comprising controlling annealing temperature during each annealing to control the flatband voltage of the high-k dielectric film.
17. (Original) The method of claim 16, further comprising controlling annealing time during each annealing to control the flatband voltage of the high-k dielectric film.